

# μPA2738GR

P-channel MOSFET

 $-30 \text{ V}, -10 \text{ A}, 15 \text{ m}\Omega$ 

R07DS0870EJ0100 Rev.1.00 Aug 28, 2012

## **Description**

The  $\mu$  PA2738GR is P-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipment.

### **Features**

- $V_{DSS} = -30 \text{ V } (T_A = 25^{\circ}\text{C})$
- Low on-state resistance
- -- R<sub>DS(on)</sub> = 15 mΩ MAX. (V<sub>GS</sub> = -10 V, I<sub>D</sub> = -10 A)
- 4.5 V Gate-drive available
- Small and surface mount package (Power SOP8)
- Pb-free and Halogen free



Power SOP8

## **Ordering Information**

Part No.	LEAD PLATING	PACKING	Package
μ PA2738GR-E1-AT	Pure Sn	Tape 2500 p/reel	Power SOP8
μ PA2738GR-E2-AT			0.08 g TYP.

## Absolute Maximum Ratings (T<sub>A</sub> = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V <sub>GS</sub> = 0 V)	V <sub>DSS</sub>	-30	V
Gate to Source Voltage (V <sub>DS</sub> = 0 V)	V <sub>GSS</sub>	∓20	V
Drain Current (DC)	I <sub>D(DC)</sub>	∓10	Α
Drain Current (pulse) *1	I <sub>D(pulse)</sub>	∓100	Α
Total Power Dissipation *2	P <sub>T1</sub>	1.1	W
Total Power Dissipation (PW = 10 sec) *2	P <sub>T2</sub>	2.5	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	−55 to +150	°C
Single Avalanche Current *3	I <sub>AS</sub>	10	Α
Single Avalanche Energy *3	E <sub>AS</sub>	10	mJ

### **Thermal Resistance**

Channel to Ambient Thermal Resistance \*2 Rth(ch-A) 114 °C/W

Notes: \*1. PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

\*2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt

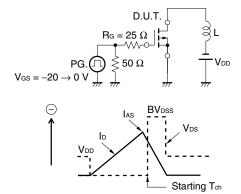
\*3. Starting  $T_{ch}$  = 25°C,  $V_{DD}$  = -15 V,  $R_G$  = 25  $\Omega$ ,  $V_{GS}$  = -20  $\rightarrow$  0 V, L = 100  $\mu H$ 

## Electrical Characteristics (T<sub>A</sub> = 25°C)

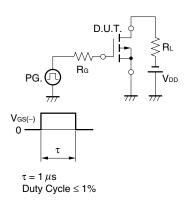
Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			-1	μΑ	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$
Gate Leakage Current	I <sub>GSS</sub>			∓100	nA	$V_{GS} = \mp 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	$V_{GS(off)}$	-1.0		-2.5	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$
Forward Transfer Admittance *1	y <sub>fs</sub>	4			S	$V_{DS} = -10 \text{ V}, I_{D} = -5.0 \text{ A}$
Drain to Source On-state	R <sub>DS(on)1</sub>		12	15	mΩ	$V_{GS} = -10 \text{ V}, I_D = -10 \text{ A}$
Resistance *1	R <sub>DS(on)2</sub>		19	29	mΩ	$V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}$
Input Capacitance	C <sub>iss</sub>		1450		pF	$V_{DS} = -10 \text{ V},$
Output Capacitance	Coss		710		pF	$V_{GS} = 0 V$ ,
Reverse Transfer Capacitance	C <sub>rss</sub>		650		pF	f = 1 MHz
Turn-on Delay Time	t <sub>d(on)</sub>		14		ns	$V_{DD} = -15 \text{ V}, I_D = -5.0 \text{ A},$
Rise Time	t <sub>r</sub>		30		ns	$V_{GS} = -10 \text{ V},$
Turn-off Delay Time	t <sub>d(off)</sub>		60		ns	$R_G = 10 \Omega$
Fall Time	t <sub>f</sub>		50		ns	
Total Gate Charge	$Q_{G}$		37		nC	$V_{DD} = -24 \text{ V},$
Gate to Source Charge	Q <sub>GS</sub>		2.5		nC	$V_{GS} = -10 \text{ V},$
Gate to Drain Charge	$Q_{GD}$		20		nC	$I_{D} = -10 \text{ A}$
Body Diode Forward Voltage *1	$V_{F(S-D)}$		0.86		V	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V
Reverse Recovery Time	t <sub>rr</sub>		47		ns	$I_F = 10 \text{ A}, V_{GS} = 0 \text{ V},$
Reverse Recovery Charge	Q <sub>rr</sub>		43		nC	di/dt = 100 A/μs

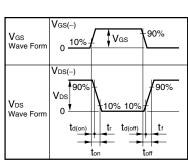
Note: \*1. Pulsed

## **TEST CIRCUIT 1 AVALANCHE CAPABILITY**



## **TEST CIRCUIT 2 SWITCHING TIME**





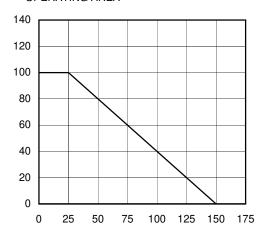
## **TEST CIRCUIT 3 GATE CHARGE**

$$\begin{array}{c|c} D.U.T. \\ \hline \\ IG = -2 \text{ mA} \\ \hline \\ \hline \\ PG. \\ \hline \\ \end{array}$$

dT - Percentage of Rated Power - %

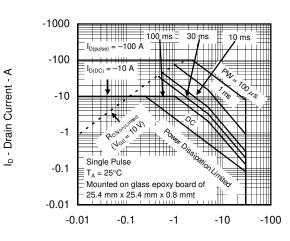
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

# DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



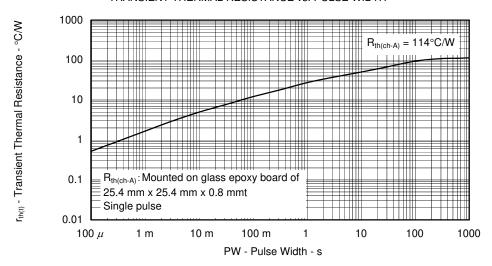
T<sub>A</sub> - Ambient Temperature - °C

### FORWARD BIAS SAFE OPERATING AREA

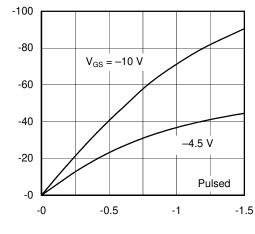


V<sub>DS</sub> - Drain to Source Voltage - V

#### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

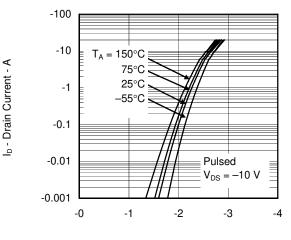


# DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



V<sub>DS</sub> - Drain to Source Voltage - V

### FORWARD TRANSFER CHARACTERISTICS



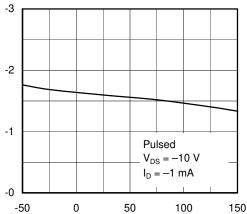
 $V_{\text{GS}}$  - Gate to Source Voltage - V

I<sub>D</sub> - Drain Current - A

V<sub>GS(off)</sub> - Gate to Source Cut-off Voltage - V

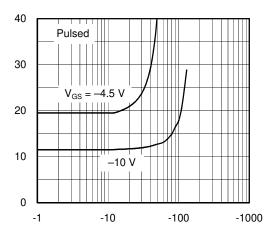
 $R_{\text{DS}(\text{on})}$  - Drain to Source On-state Resistance -  $m\Omega$ 

## GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



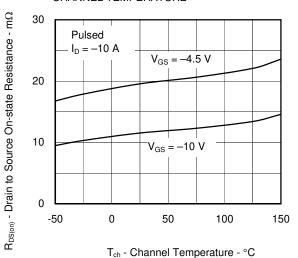
T<sub>ch</sub> - Channel Temperature - °C

# DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

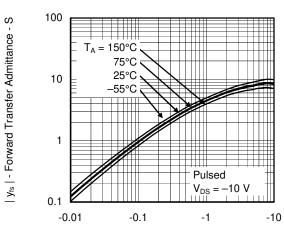


# DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

ID - Drain Current - A

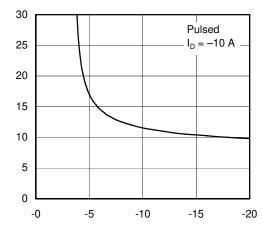


# FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



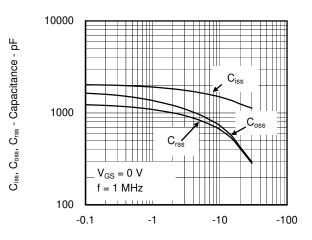
ID - Drain Current - A

# DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



 $V_{\text{GS}}$  - Gate to Source Voltage - V

### CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

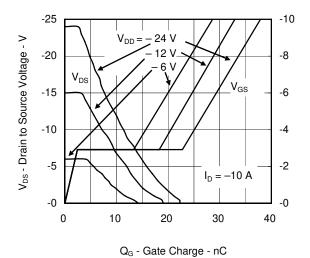


V<sub>DS</sub> - Drain to Source Voltage - V

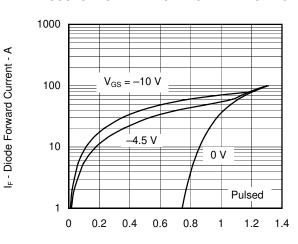
R<sub>DS(on)</sub> - Drain to Source On-state Resistance - mΩ

### DYNAMIC INPUT/OUTPUT CHARACTERISTICS

### SOURCE TO DRAIN DIODE FORWARD VOLTAGE



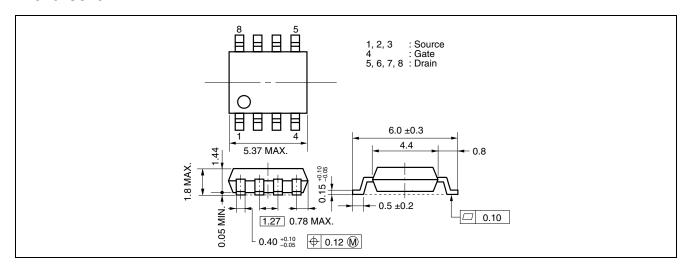




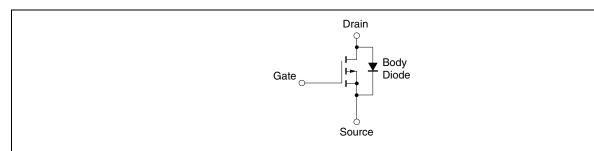
 $V_{\text{F(S-D)}}$  - Source to Drain Voltage - V

## Package Drawings (Unit: mm)

## **Power SOP8**



## **Equivalent Circuit**



**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

**Revision History** 

## $\mu$ PA2738GR Data Sheet

		Description		
Rev.	Date	Page	Summary	
1.00	Aug 28, 2012	_	First Edition Issued	

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